

ABSTRACT OF THE DISCLOSURE

A group-III nitride semiconductor stack comprises a single-crystal substrate, a first group-III nitride layer
5 formed on a principal surface of the single-crystal substrate, a graded low-temperature deposited layer formed on the group-III nitride layer and made of nitride in which group-III element composition is continuously changed, and a second group-III nitride layer formed on the graded low-temperature
10 deposited layer.